

# Dual Supply, 2-Bit Voltage Translator / Buffer / Repeater / I<sup>2</sup>C Application

## FXMA2102

### Description

The FXMA2102 is a high performance configurable dual voltage supply translator for bi-directional voltage translation over a wide range of input and output voltages levels.

Intended for use as a voltage translator between I<sup>2</sup>C Bus compliant masters and slaves.

The device is designed so that the A port tracks the V<sub>CCA</sub> level and the B port tracks the V<sub>CCB</sub> level. This allows for bi-directional A/B port voltage translation between any two levels from 1.65 V to 5.5 V. V<sub>CCA</sub> can equal V<sub>CCB</sub> from 1.65 V to 5.5 V. The OE pin is referenced to V<sub>CCA</sub>.

Either V<sub>CC</sub> can be powered up first. Internal power down control circuits place the device in 3-state if either V<sub>CC</sub> is removed.

The two ports of the device have automatic direction sense capability. Either port may sense an input signal and transfer it as an output signal to the other port.

### Features

Bi-Directional Interface between AnVt / TT7 1 Tf10 0 0 10 70.2992 261.4678 Tm-0006 Tc(Supports I)T $\beta$  0 0 8 111.3449 264.5292 Tm

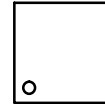


UQFN8, 1.4x1.2, 0.4P  
CASE 523AS



UQFN8 1.6X1.6, 0.5P  
CASE 523AY

### MARKING DIAGRAM



-  
-

### ORDERING INFORMATION

2 kV CDM (per JESD22-C101)

# FXMA2102

## BLOCK DIAGRAM

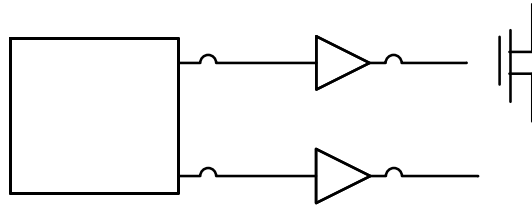


Figure 1. Block Diagram, 1 of 2 Channels





# FXMA2102

## FUNCTIONAL DESCRIPTION

### Power-Up/Power-Down Sequencing

FXM translators offer an advantage in that either  $V_{CC}$  may be powered up first. This benefit derives from the chip design. When either  $V_{CC}$  is at 0 V, outputs are in a high impedance state. The control input (OE) is designed to track the  $V_{CCA}$  supply. A pull down resistor tying OE to GND should be used to ensure that bus contention, excessive currents, or oscillations do not occur during power up/power down. The size of the pull down resistor is based upon the current sinking capability of the device driving the OE pin.

The recommended power up sequence is:

1. Apply power to the first  $V_{CC}$ .
2. Apply power to the second  $V_{CC}$ .
3. Drive the OE input HIGH to enable the device.

The recommended power down sequence is:

1. Drive OE input LOW to disable the device.
2. Remove power from either  $V_{CC}$ .
3. Remove power from other  $V_{CC}$ .

NOTE:

4. Alternatively, the OE pin can be hardwired to  $V_{CCA}$  to save GPIO pins. If OE is hardwired to  $V_{CCA}$ , either  $V_{CC}$  can be powered up or down first.

## APPLICATION CIRCUIT

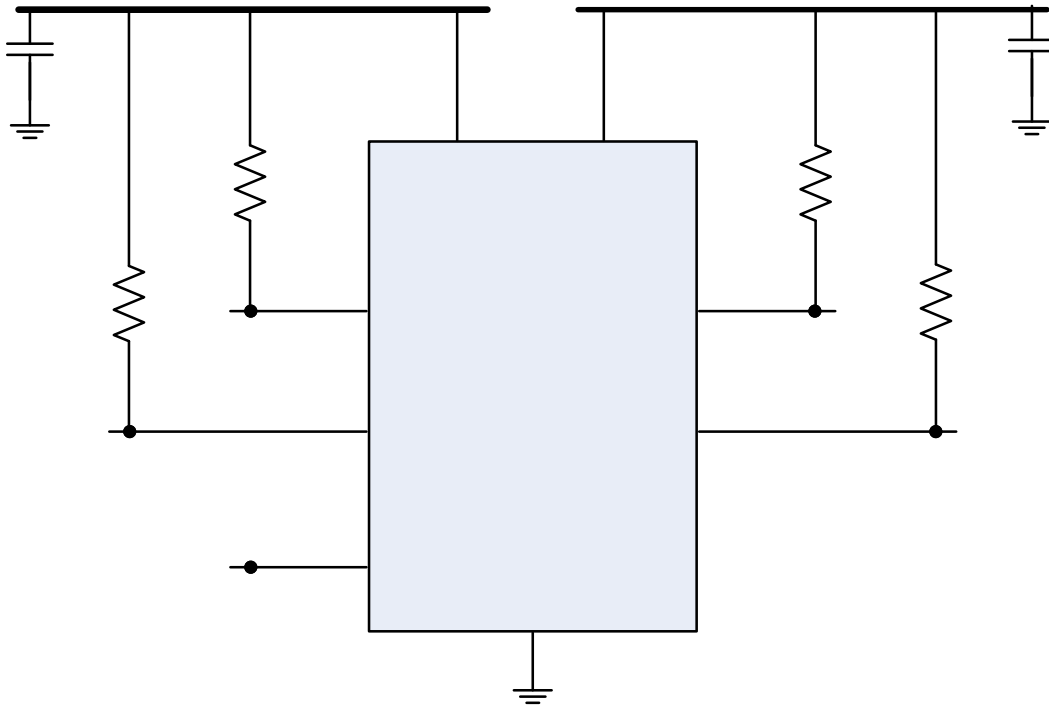


Figure 4. Application Circuit

## APPLICATION NOTES

The FXMA2102 has open drain I/Os and requires external pull up resistors on the four data I/O pins, as shown in Figure 4. If a pair of data I/O pins ( $A_n/B_n$ ) is not used, both pins should be tied to GND (or both to  $V_{CC}$ ). In this case, pull down or pull up resistors are not required. The recommended values for the pull up resistors (RPU) are 1 k $\Omega$  to 10 k $\Omega$ ; however, depending on the total bus capacitance, the user is free to vary the pull up resistor value to meet the maximum I<sup>2</sup>C edge rate per the I<sup>2</sup>C specification (UM10204 rev. 03, June 19, 2007). For example, the maximum edge rate (30% – 70%) during fast mode (400 kbit/s) is 300 ns. If bus capacitance is approaching the maximum 400 pF, lower the RPU value to keep the rise time below 300 ns (Fast Mode). Section 7.1 of the I<sup>2</sup>C specification provides an excellent guideline for pull up resistor sizing.

### Theory of Operation

The FXMA2102 is designed for high performance level shifting and buffer / repeating in an I<sup>2</sup>C application. Figure 1 shows that each bi directional channel contains two series Npassgates and two dynamic drivers. This hybrid architecture is highly beneficial in an I<sup>2</sup>C application where auto direction is a necessity.

For example, during the following three I

## FXMA2102

1.65 V and a slave on the I<sup>2</sup>C translator B port with a V<sub>CC</sub> of 3.3 V, the maximum V<sub>IL</sub> of the master is (1.65 V x 0.3) 495 mV. The slave could legally transmit a valid logic LOW of 0.4 V to the master.

If the I<sup>2</sup>C translator's channel resistance is too high, the voltage drop across the translator could present a V<sub>IL</sub> to the master greater than 495 mV. To complicate matters, the I<sup>2</sup>C

specification states that 6 mA of I<sub>OL</sub> is recommended for bus capacitances approaching 400 pF. More I<sub>OL</sub> increases the voltage drop across the I<sup>2</sup>C translator. The I<sup>2</sup>C application benefits when I<sup>2</sup>C translators exhibit low V<sub>OL</sub> performance. Figure 6 depicts typical FXMA2102 V<sub>OL</sub> performance vs. the competition, given a 0.4 V V<sub>IL</sub>.

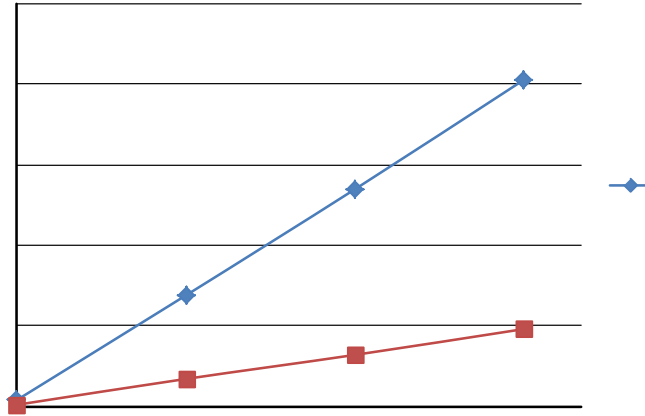


Figure 6. V<sub>OL</sub> vs. I<sub>OL</sub>

### I<sup>2</sup>C-Bus Isolation

The FXMA2102 supports I<sup>2</sup>C





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## DYNAMIC OUTPUT ELECTRICAL CHARACTERISTICS

### OUTPUT RISE / FALL TIME

Ω

-

Symbol	Parameter	V <sub>CCO</sub>				Unit
		4.5 to 5.5 V	3.0 to 3.6 V	2.3 to 2.7 V	1.65 to 1.95 V	
		Typ	Typ	Typ	Typ	

## DYNAMIC OUTPUT ELECTRICAL CHARACTERISTICS

### MAXIMUM DATA RATE

Ω

-

V <sub>CCA</sub>	Direction	V <sub>CCB</sub>				Unit
		4.5 to 5.5 V	3.0 to 3.6 V	2.3 to 2.7 V	1.65 to 1.95 V	
		Min	Min	Min	Min	



**CAPACITANCE**

Symbol	Parameter

T  
SIG

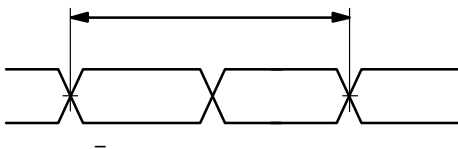
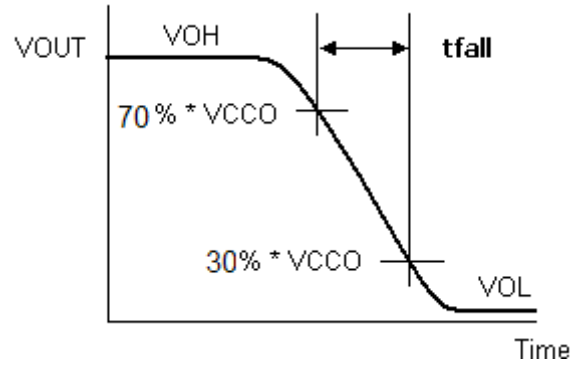
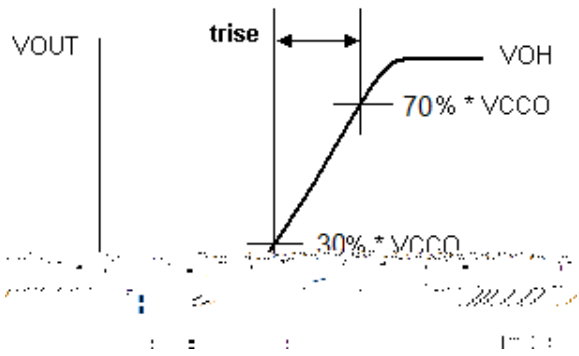
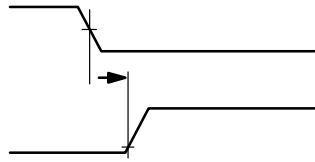
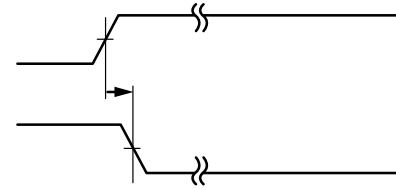
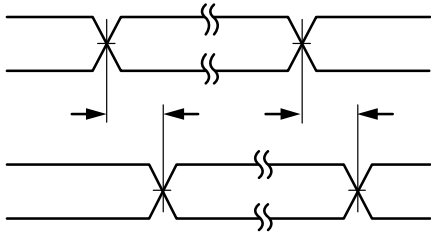
**Table 1. PROPAGATION DELAY TABLE**

Test

**Table 2. AC LOAD TABLE**

V <sub>CC0</sub>	C <sub>L</sub>	R <sub>L</sub>

TIMING DIAGRAMS



# FXMA2102

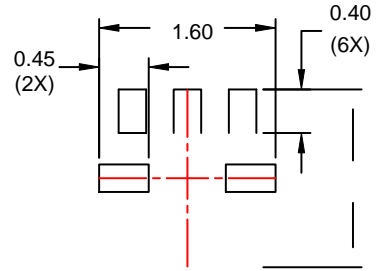
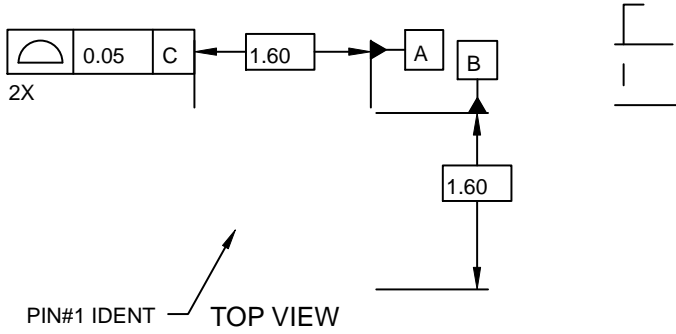
## ORDERING INFORMATION

Part Number	Operating Temperature Range	Top Mark	Package	Packing Method
	-		-	
			-	

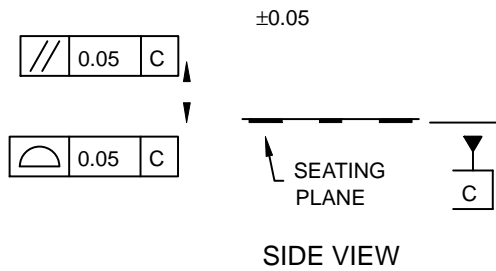
**UQFN8, 1.40x1.20, 0.40P**  
CASE 523AS  
ISSUE B

**UQFN8 1.6X1.6, 0.5P**  
CASE 523AY  
ISSUE O

DATE 31 AUG 2016

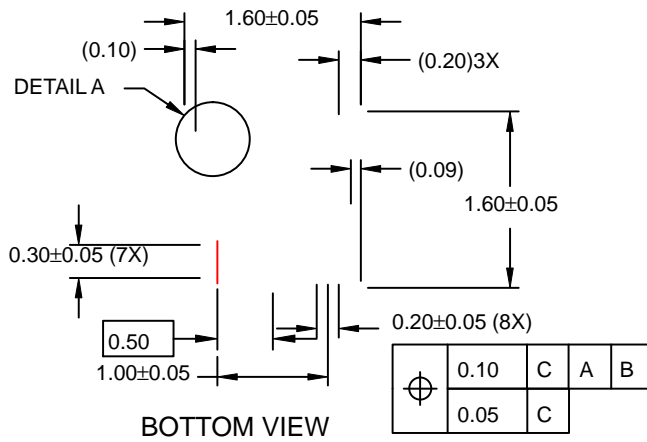


**RECOMMENDED  
LAND PATTERN**



**NOTES:**

A. PACKAGE CONFORMS TO JEDEC MO-



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